Dual P-Channel 60-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical	Appl	ications:
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- White LED boost converters
- · Automotive Systems
- Industrial DC/DC Conversion Circuits

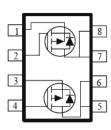
PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I□ (A)		
-60	44 @ V _{GS} = -10V	-6.2		
	$52 @ V_{GS} = -4.5V$	-5.7		



RoHS COMPLIANT HALOGEN FREE







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			-60	V		
Gate-Source Voltage	V_{GS}	±20	V			
Continuous Drain Current ^a	T _A =25°C		-6.2			
Continuous Drain Current	T _A =70°C	· I _D	-5	Α		
Pulsed Drain Current ^b	I _{DM}	-30				
Continuous Source Current (Diode Conduction) a	I _S	-4.6	Α			
Device Discinction ^a	T _A =25°C		2.5	· W		
Power Dissipation ^a	T _A =70°C	l P	1.6			
Operating Junction and Storage Temperature Range		T _J , T _{sta}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	50	°C/W			
Maximum Junction-to-Ambient	Steady State	ГХ⊕ЈА	90				

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

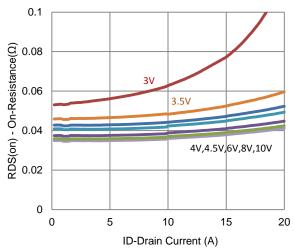
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zara Cata Valtaga Drain Current	ı	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}$			-1 uA		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-25	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-10			Α	
Drain Cauras On Basistanas a	r	$V_{GS} = -10 \text{ V}, I_D = -5.2 \text{ A}$			44	mΩ	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -4.2 \text{ A}$			52	11122	
Forward Transconductance a	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -5.2 \text{ A}$		18		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = -2.3 \text{ A}, V_{GS} = 0 \text{ V}$		-0.78		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = -30 \text{ V}, V_{GS} = -4.5 \text{ V},$		28		nC	
Gate-Source Charge	Q_{gs}	$I_{DS} = -30 \text{ V}, \text{ V}_{GS} = -4.3 \text{ V},$ $I_{D} = -5.2 \text{ A}$		6.7			
Gate-Drain Charge	Q_gd	1 _D = 3.2 A		12			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = -30 \text{ V}, R_{L} = 5.9 \Omega,$		10			
Rise Time	t _r	$V_{DS} = -30 \text{ V}, K_L - 3.9 \Omega,$ $I_D = -5.2 \text{ A},$		14		ne	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		102		ns	
Fall Time	t _f	V GEN - 10 V, T GEN - 0 12		39			
Input Capacitance	C _{iss}			1226			
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		182		pF	
Reverse Transfer Capacitance	C_{rss}			158			

Notes

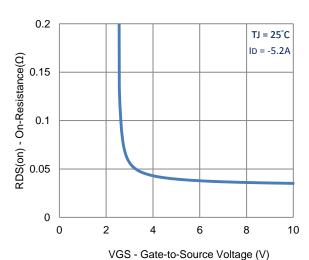
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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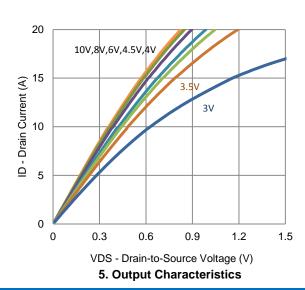
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage

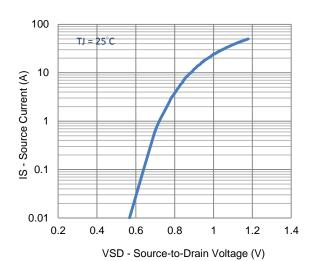


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TJ = 25°C

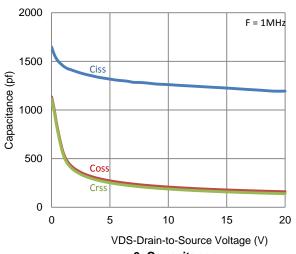
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0 0 1 2 3 4 5

VGS - Gate-to-Source Voltage (V)

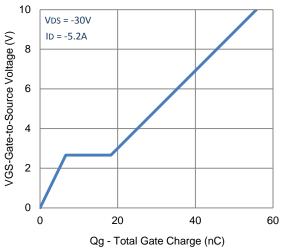
2. Transfer Characteristics



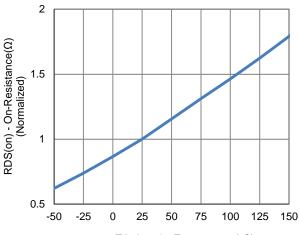
4. Drain-to-Source Forward Voltage



Typical Electrical Characteristics

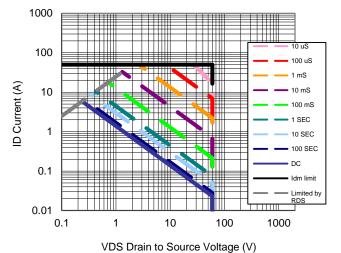




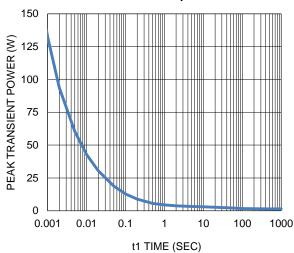


TJ -JunctionTemperature(°C)

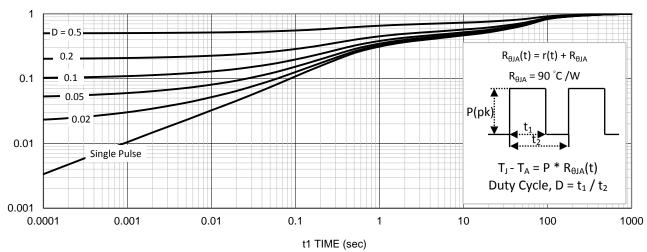




9. Safe Operating Area

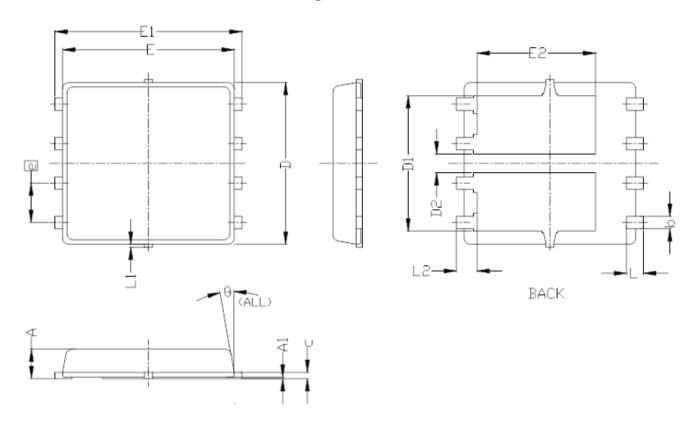


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES				
SYMBOLS	MIN	NOM	MAX	MIN	NOM	MAX		
A	0.85	0. 95	1.00	0.033	0.037	0.039		
A1	0.00		0.05	0.000		0.002		
b	0.30	0.40	0.50	0.012	0.016	0.020		
c	0. 15	0.20	0. 25	0.006	0.008	0.010		
D	5. 20 BSC			0. 205 BSC				
D1	4. 35 BSC			0. 171 BSC				
D2	0.50	0.60	0.75	0.020	0.024	0.030		
Е	5. 55 BSC			0. 219 BSC				
E1		6. 05 BSC			0. 238 BSC			
E2	3.82 BSC			0. 150 BSC				
e	1. 27 BSC			0.050 BSC				
L	0.45	0.55	0.65	0.018	0.022	0.026		
L1	0		0. 15	0		0.006		
L2	0. 68 REF			0.027 REF				
θ	0°		10°	0°		10°		